

Space Charge, Beam Loading and the Correction of Phase Shift and Bunch Form Deformation in a Double Harmonic RF System

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Introduction

Parameters of the synchrotron SIS-100:

Circumference: 1086 m

Heavy ions

Max. intensity: $5.0 \cdot 10^{11}$

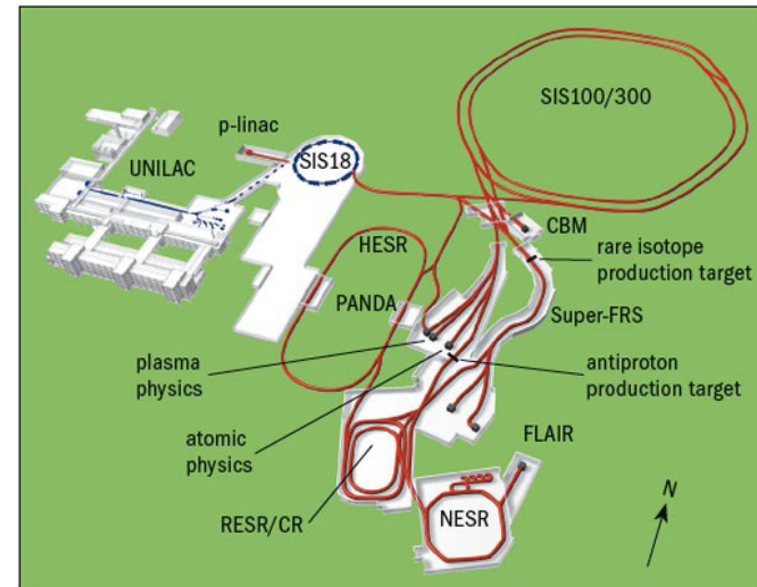
Energy E_{kin} : (0.2 - 1.5) GeV/u

Operating RF

Frequency f_{RF} : (1.5 - 2.6) MHz

Momentum

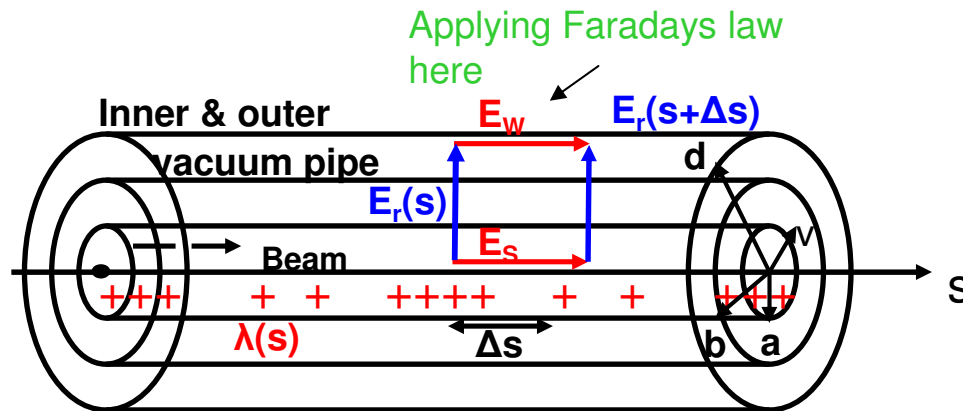
spread δ : $5.0 \cdot 10^{-4}$



Source: Web

- $\hat{U}_{\text{RF}} = 178 \text{ kV}$ for given δ and $h = 10$ so that bucket area of 8 buckets is equal to that of the coasting beam
- Ion beam with the current $I_B = e\lambda(s)\beta c$ circulating in a beam pipe

Space charge



- For small perturbations of $\lambda(s)$:
Using Gauß' and Ampère's law for the quasi-static case

$$E_r = \frac{e\lambda(s)}{2\pi\epsilon_0} \frac{1}{r} \quad B_\phi = \frac{\mu_r\mu_0 e\lambda(s)\beta c}{2\pi} \frac{1}{r} \quad r \geq a$$

$$E_r = \frac{e\lambda(s)}{2\pi\epsilon_0} \frac{r}{a^2} \quad B_\phi = \frac{\mu_0 e\lambda(s)\beta c}{2\pi} \frac{r}{a^2} \quad r \leq a$$

Faradays' law: $\oint_{\text{Line}} \vec{E} d\vec{l} = -\frac{\partial}{\partial t} \int_{\text{Surface}} \vec{B} d\vec{\sigma} = -\frac{\partial}{\partial t} \Delta s \int_0^b B_\phi dr$

With $-\frac{\partial \lambda}{\partial t} = -\frac{\partial \lambda}{\partial s} \frac{ds}{dt} = -\beta c \frac{\partial \lambda}{\partial s}$ and $g_0 = 1 + 2 \ln \frac{b}{a}$ as geometry factor for a circular vacuum pipe.

$$E_s - E_w = -\frac{eg_0}{4\pi\epsilon_0\gamma^2} \left[1 + \frac{2\gamma^2}{g_0\epsilon_r} \ln \frac{d}{b} \right] \frac{\partial \lambda(s)}{\partial s} + 2e\beta^2 c^2 \frac{L}{2\pi R} \frac{\partial \lambda(s)}{\partial s}$$

R: Mean radius of synchrotron

Passive space charge compensation

- The total voltage per turn is:

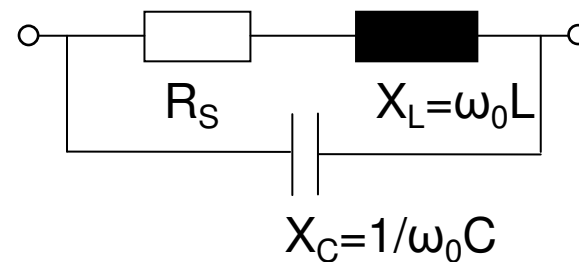
$$U_s - U_w = -e\beta c R \frac{\partial \lambda(s)}{\partial s} \left[\frac{g_0 Z_0}{2\beta\gamma^2} - \omega_0 L \right]$$

- *For compensation the impedance term in the brackets must be zero!*

- For a given length l the dimensions of the insert can be evaluated by the following formula:

$$L = \mu_r L_0 = (\mu_r' - i\mu_r'') \frac{\mu_0 l}{2\pi} \ln \frac{d}{b}$$

Serial equivalent circuit of the inductive impedance



Material

Ferromagnetic and magnetic alloy material with a frequency dependent complex permeability was measured: d: 660 mm, b: 290 mm, thickness: 25 mm

MN8CX soft magnetic MnZn ferrite:

Broadband ferrite with high permeability.

FINEMET® FT3-M magnetic alloy:

Real part permeability μ' seven times higher than for MnZn ferrite.

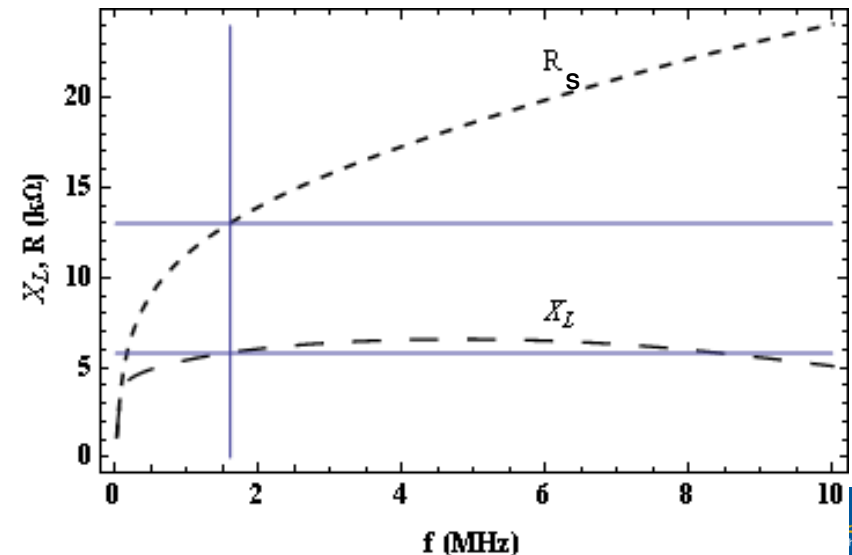
Therefore material of choice.



Impedances

Koba et al., Rev. Sci. Instrum., Vol. 70, No. 7 (1999)

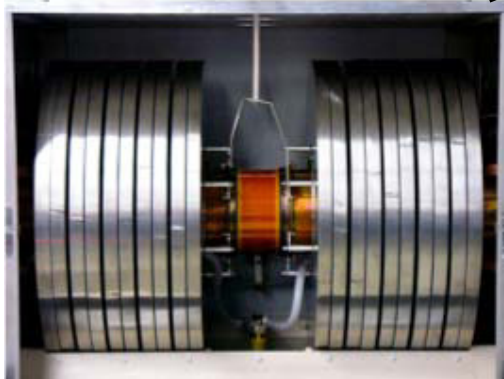
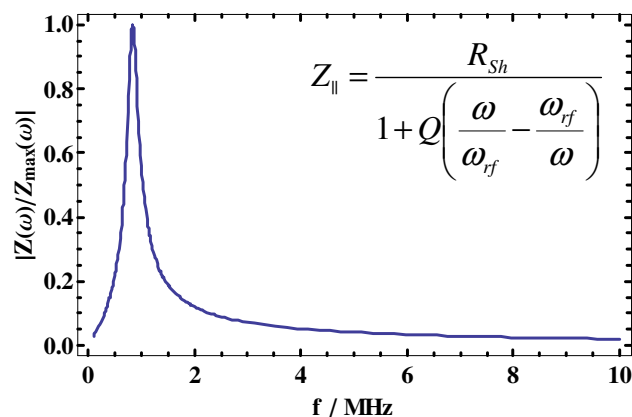
- Impedance tuner installed in the KEK PS.
- 12 Finemet ring cores.
- SIS-100: 78 ring cores necessary for 2 m insert length.
- Complex impedance: $Z_{||}(f) = R_S(f) + iX_L(f)$
 $f_{RF} = f = 10 * f_0 = 1.57 \text{ MHz}$
 $X_L = 6.4 \text{ k}\Omega$
 $R_S = 13.0 \text{ k}\Omega$
— Values of X_L and R_S @ f_{RF}



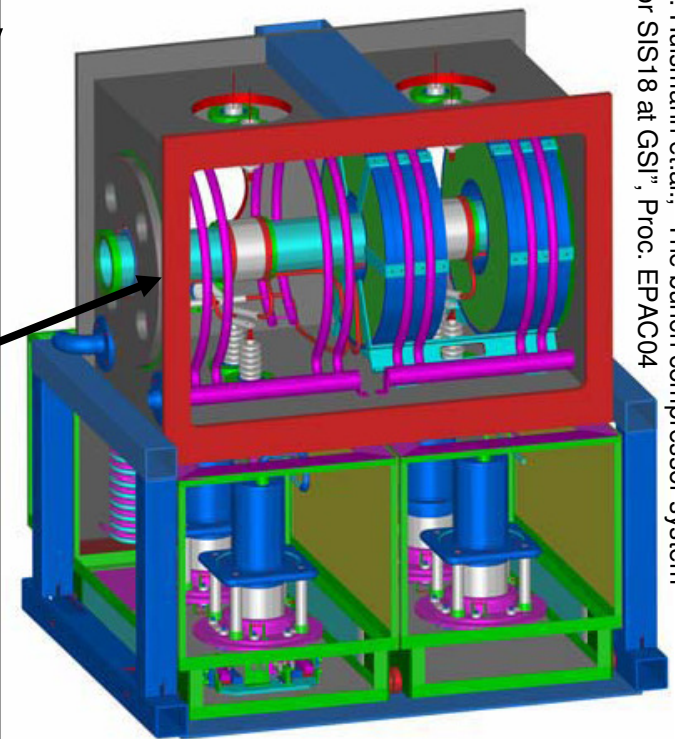
Cavity impedance

Example of an existing cavity with amplifier:

- Determined in addition to the ring cores and the gap by the RF power station
- E.g.: Bunch Compressor cavity SIS18
- Ring cores 2 k Ω shunt impedance per half cavity
- About 1 k Ω per half amplifier
- Makes about 2 k Ω for the total cavity
- Quality factor $Q = 4.2$ @ 839 kHz



Ch.Dimopoulou, "On behalf of FAIR Technical Division, GSI Accelerator Division & collaborators...", RuPAC08



P. Hülsmann et.al., "The bunch compressor system for SIS18 at GSI", Proc. EPAC04

Potential-well distortion

- Potential-well distortion: Alteration of bunch distribution.
- Influence of time-independent perturbation of wake potential to the ion bunch.
- Static perturbation changes the shape of the bunch.
- Self-consistent solution for a Gaussian ion density distribution is the Haissinski equation:

$$\lambda(\tau) = \lambda(0) \exp \left[- \left(\frac{\omega_{s0} \beta^2 E_0}{\eta \sigma_E} \right)^2 \frac{\tau^2}{2} + \frac{e^2 \beta^2 E_0}{2\pi \eta T_0 \sigma_E^2} \int_0^\tau d\tau'' \int_{\tau''}^\infty d\tau' \rho(\tau') \int_{-\infty}^\infty d\omega Z_0^{\parallel}(\omega) e^{-i\omega(\tau' - \tau'')} \right]$$

- Expression in brackets describes the motion of a particle in a potential-well.

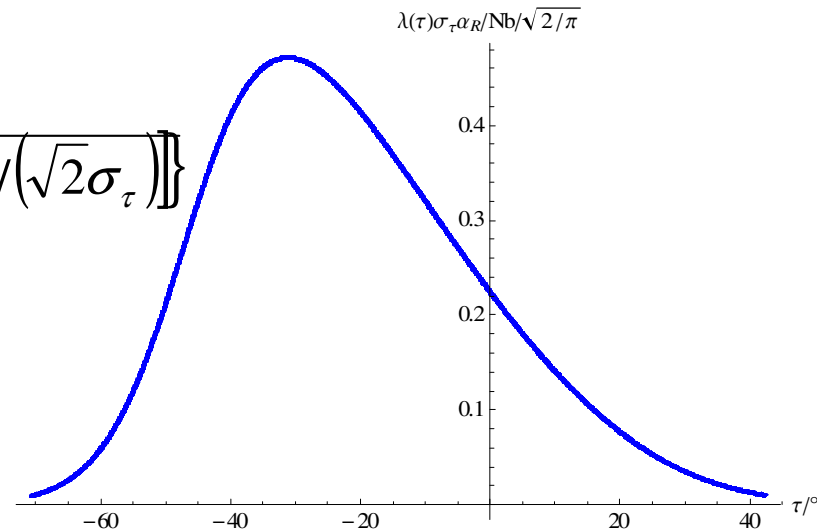
Potential-well distortion

- Purely inductive longitudinal impedance, $Z_0^{\parallel}(\omega) = X_L$
 - Distribution will stay left-right symmetric
 - Bunch lengthening or shortening
- Purely resistive longitudinal impedance, $Z_0^{\parallel}(\omega) = R_s$
 - Parasitic loss of the beam particle, which is largest at the peak
 - Peak moves forward above transition and backward below transition

$$\lambda(\tau) = \frac{\sqrt{2/\pi} e^{-\tau^2/(2\sigma_\tau^2)}}{\alpha_R \sigma_\tau \left\{ \coth(\alpha_R N/2) - \operatorname{erf}\left[\tau/(\sqrt{2}\sigma_\tau)\right] \right\}}$$

$$\sigma_\tau = \frac{|\eta| \sigma_E}{\beta^2 \omega_{s0} E_0}, \quad \alpha_R = \frac{e^2 \beta^2 E_0 R_s}{\eta T_0 \sigma_E^2}$$

$$\operatorname{erf}(x) = \frac{2}{\sqrt{\pi}} \int_0^x e^{-t^2} dt$$

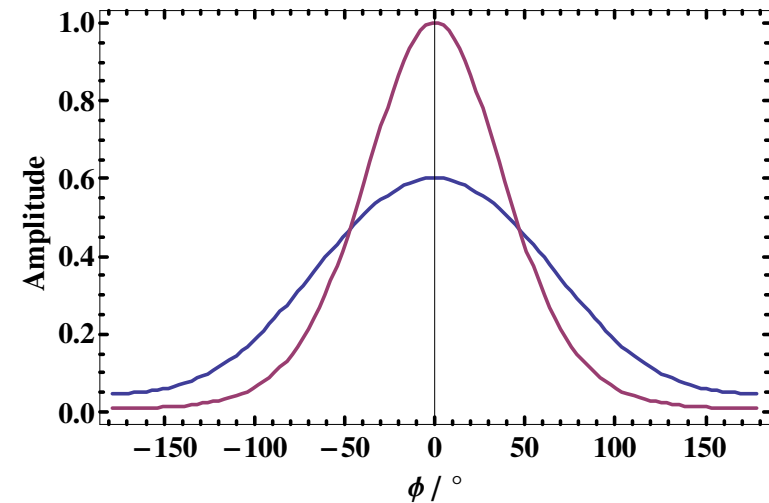


K. Y. Ng, "Physics of Intensity Dependent Beam Instabilities",
(World Scientific, Singapore, 2006)

Single harmonic RF system

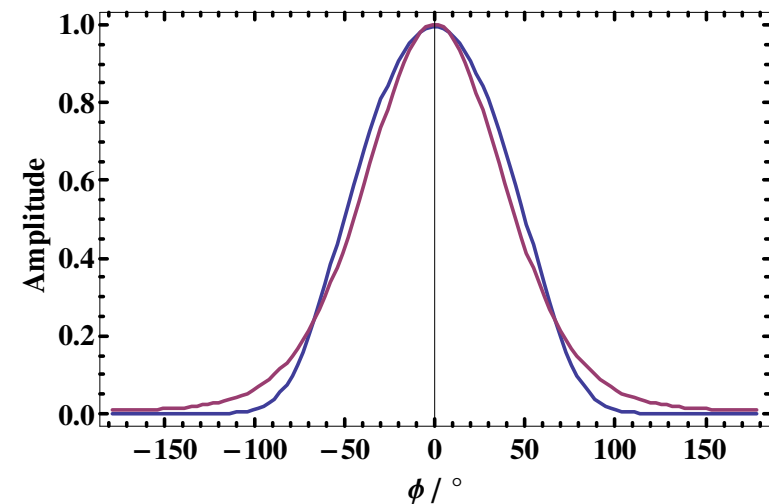
Without sc compensating insert:

Lower peak current and bunch-lengthening by sc in a single harmonic system. $Z_0^{\parallel}(\omega) = X_C$



With sc compensating insert (ideal imaginary one): $Z_0^{\parallel}(\omega) = X_L$

Comparing the blue curve in the top figure with the one in the bottom figure by imaginary part of insert sc impedance is fully compensated.



- Line charge density distribution with low sc impedance
- Line charge density distribution with high sc impedance

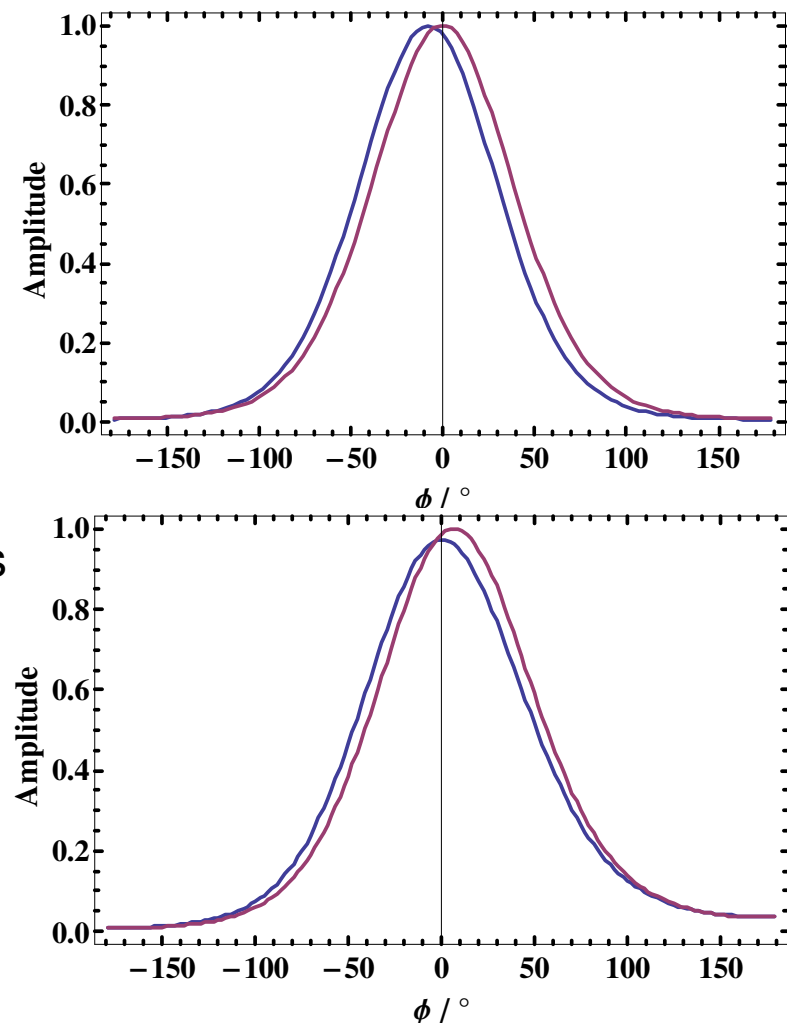
Single harmonic RF system

Effect of resistive part of insert impedance in addition to the imaginary part:

- Peak moves backwards compared to the sc free distribution in red
- Phase shift ($\sim 10^\circ$ for 10^{10} U^{28+} , $\Sigma \approx 0.03$)

sc parameter Σ defined as: $\Sigma = \frac{1}{\frac{V_{RF}}{V_{SC}} - 1}$

- This can be corrected by giving the synchronous phase Φ_S of the RF voltage a shift of -0.12 rad.
- Asymmetric bunch form not correctable; it increases because of accelerated bucket form.
- With a space charge parameter of about $\Sigma = 0.08$ the bunch form starts to become asymmetric.



— Line charge density distribution with low sc impedance
— Line charge density distribution with high sc impedance

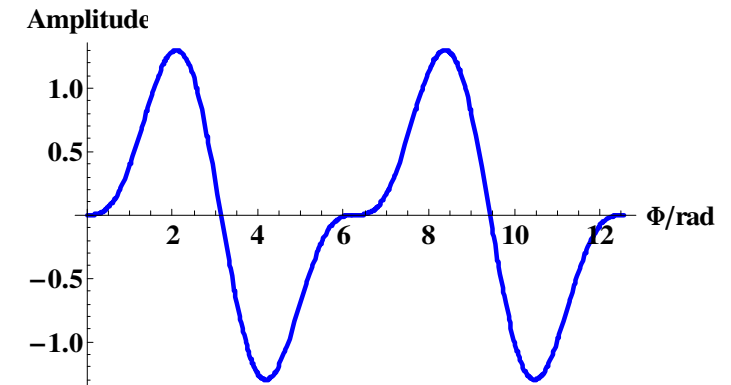
Double harmonic RF system

- Voltage of a double harmonic system $V(\Phi) = \sin \Phi - \sin \Phi_s - \alpha \left\{ \sin \left[\Phi_{s2} + \frac{h_2}{h_1} (\Phi - \Phi_s) \right] - \sin \Phi_{s2} \right\}$

- Synchronous phases of the 2 harmonics:

$$\Phi_s = \Phi_{s2} = 0, \alpha = V_2/V_1 = 0.5, h_2/h_1 = 2$$

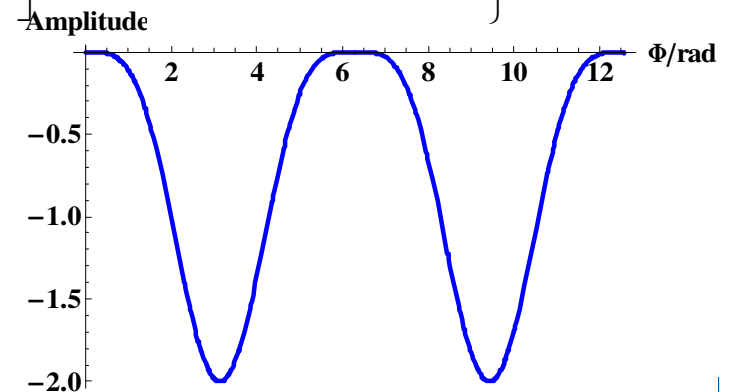
- An area with no RF voltage appears comparable to a small barrier bucket region



- The RF potential then is

$$Y(\Phi) = \cos \Phi - \cos \Phi_s + (\Phi - \Phi_s) \sin \Phi_s - \alpha \frac{h_1}{h_2} \left\{ \cos \left[\Phi_{s2} + \frac{h_2}{h_1} (\Phi - \Phi_s) \right] - \cos \Phi_{s2} + (\Phi - \Phi_s) \sin \Phi_{s2} \right\}$$

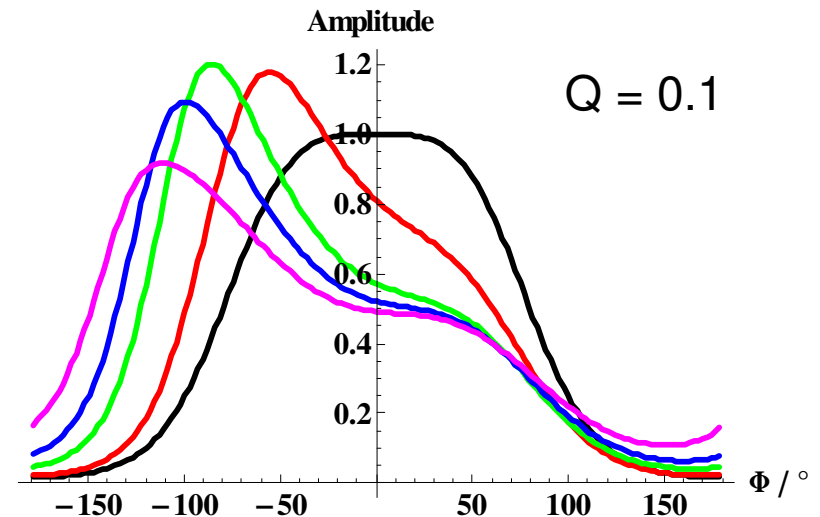
- In the potential free area $\lambda(\tau) = \frac{\lambda_0}{1 + \alpha_R N_b \lambda_0 \tau}$ is the beam profile



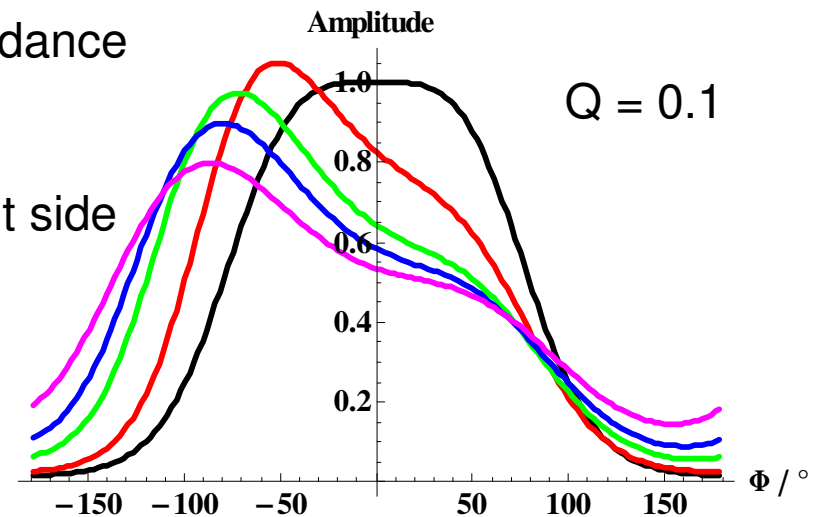
K. Y. Ng, "Physics of Intensity Dependent Beam Instabilities",
(World Scientific, Singapore, 2006)

Double harmonic RF system

- Only potential-well distortion
- Interaction with the resistive part of the longitudinal impedance
- Haissinski equation only contains resistive part
- This leads to asymmetry in the beam profile



- Potential-well distortion and space charge impedance
- Shorter bunch length because of capacitive space charge impedance below transition
- Lower peak amplitude but amplitude on the right side of the beam distribution higher



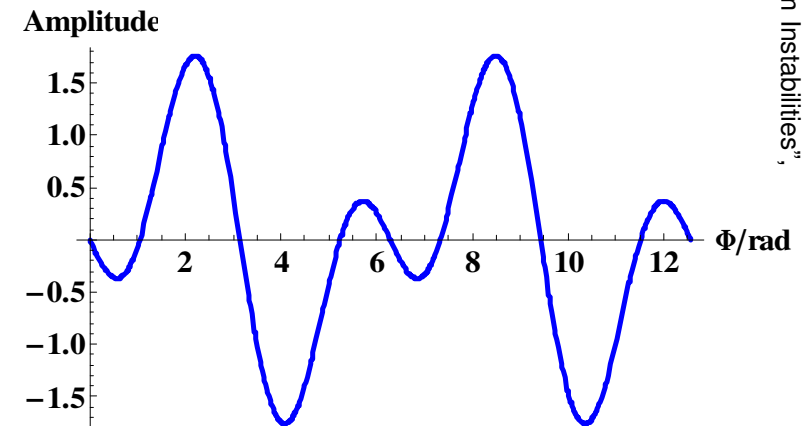
- Undisturbed double harmonic beam distribution
- $\Sigma = 0.1$: double harmonic beam distribution
- $\Sigma = 0.3$: double harmonic beam distribution
- $\Sigma = 0.5$: double harmonic beam distribution
- $\Sigma = 1.0$: double harmonic beam distribution

Double harmonic RF system

- Such asymmetric beam profiles were also observed in a barrier bucket system of the Fermilab Recycler Ring.
- The asymmetric beam profile could be compensated by adding a small voltage into the RF free region.

$$V_b = \frac{\eta \sigma_E^2 T_0}{2 \beta^2 E_0 T_2} \alpha_R N_b = \frac{e N_b R_S}{T_2}$$

- Restores the energy dissipated by the beam to the resistive part of the circumference
- Voltage of a double harmonic system with $\alpha = 1.0$ is doing this by itself.
- Adding synchrotron frequency spread into this region

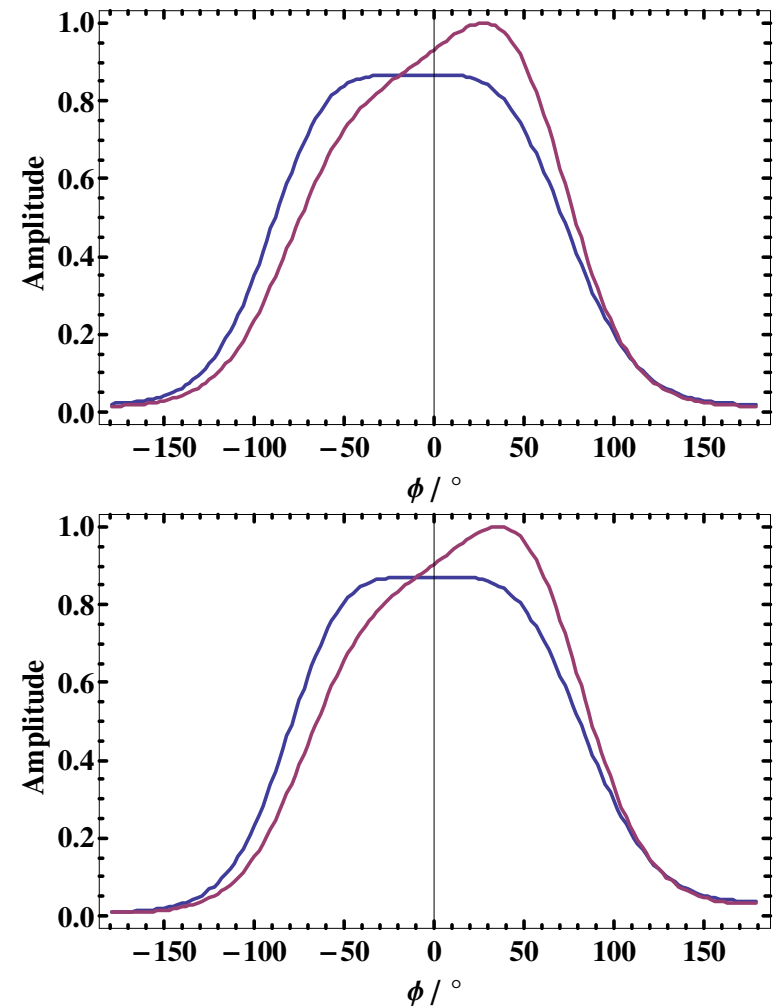


K. Y. Ng, "Physics of Intensity Dependent Beam Instabilities",
(World Scientific, Singapore, 2006)

Double harmonic RF system

- $\alpha = 0.5$, only potential-well distortion
- Correction of asymmetric beam profile through phase between the two harmonics $\Delta\Phi_S$
- Phase shift can be seen after this correction
- By correction beam distribution without sc is shifted to the right (red line)

- $\alpha = 0.5$, only potential-well distortion
- Correction of phase shift through tuning of synchronous phase Φ_S of the main harmonic
- Because of the correction the distribution with low sc in red now is asymmetric in the opposite direction
- The distribution with sc is flat



— Line charge density distribution with low sc impedance
— Line charge density distribution with high sc impedance

Double harmonic RF system

- In the following a numerical program was used to get the static beam profile distribution by solving the Haissinski equation for different sc parameters Σ starting from 0.05 up to 1.35 in steps of 0.05

Steps in short:

- The start values of $Y_{BL}(\Phi)$, $Y_{RF}(\Phi)$ for given impedances and voltages are determined by using FFT
- These values are included into the Haissinski equation giving the line charge density $\lambda(\Phi)$
- Inverse FFT of the FFT of $\lambda(\Phi)$ multiplied with impedance $Z_0^{\parallel}(\Phi)$ gives the new $Y_{BL}(\Phi)$
- This value goes back into the Haissinski equation and so on till convergence is reached

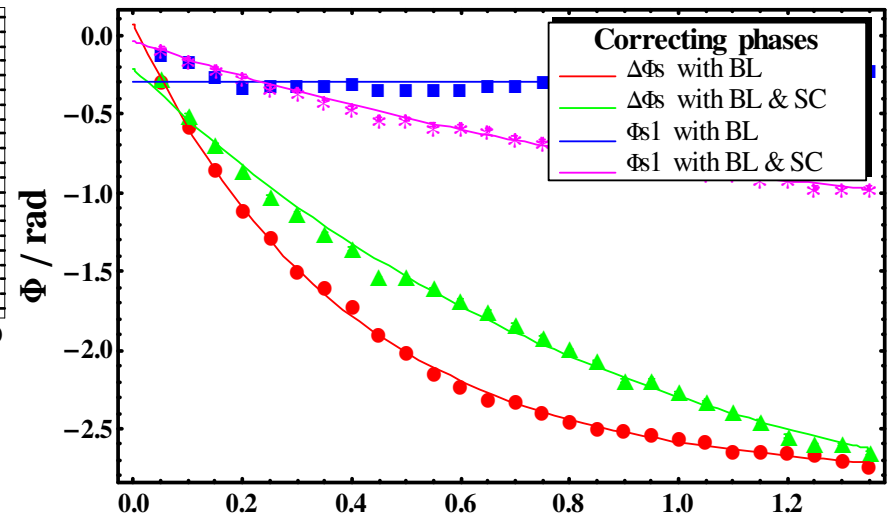
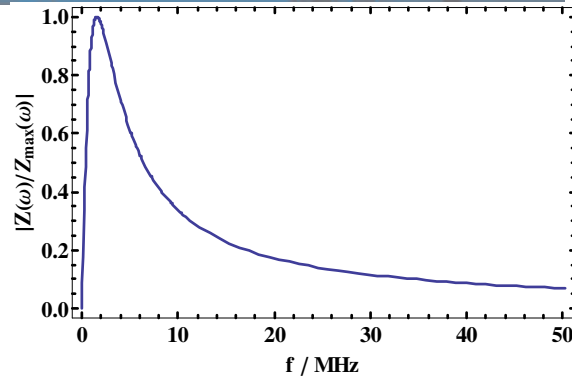
Double harmonic RF system

Characteristics of the following 4 figures:

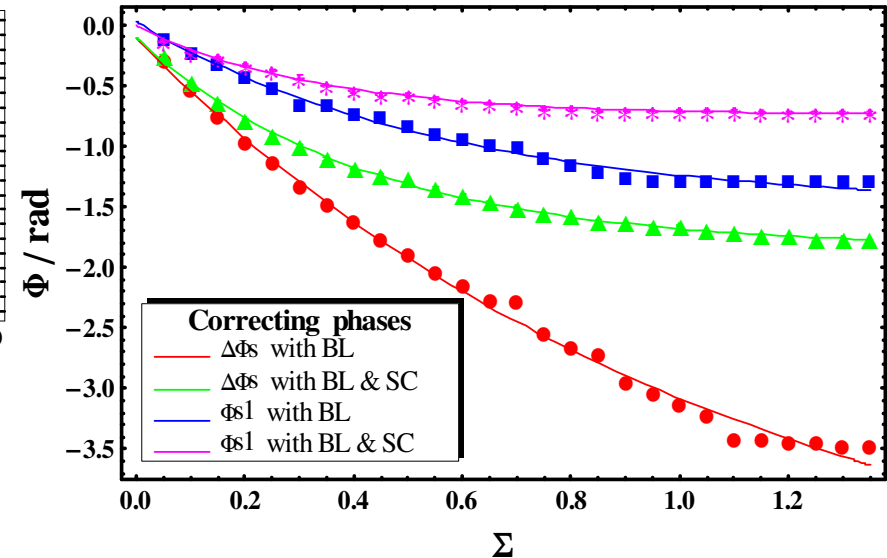
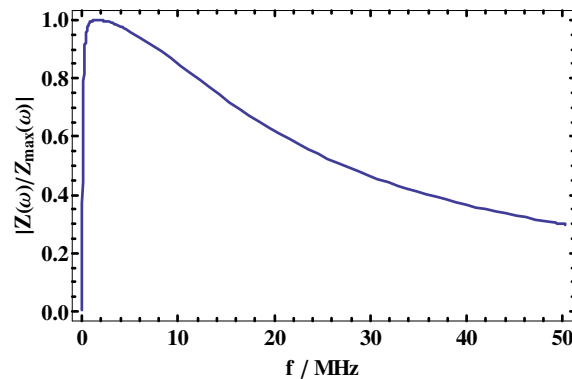
- The correction phases $\Delta\Phi_S = \Phi_S - \Phi_{S2}$ and Φ_S for different impedances over the space charge parameter Σ were collected
- $Z_{||} = \frac{R_{Sh}}{1 + Q\left(\frac{\omega}{\omega_{rf}} - \frac{\omega_{rf}}{\omega}\right)}$ has been used for $R_{Sh} = 16\text{k}\Omega$, $Q = 0.45$ and $Q = 0.1$ @ $f_{RF} = 1.57 \text{ MHz}$.
- The impedance table evaluated by the measured Finemet ring core values was used (frequency response on transparency 6).
- An impedance table with a constant resistive value over the frequency points was used ($R_{Sh} = 16 \text{ k}\Omega$).
- Values with and without taking space charge into account.
- For the fit curves the function $\left. \begin{matrix} \Delta\Phi_S \\ \Phi_S \end{matrix} \right\} = -a + be^{-k\Sigma}$ has been used.

Double harmonic RF system

$Q = 0.45$



$Q = 0.10$

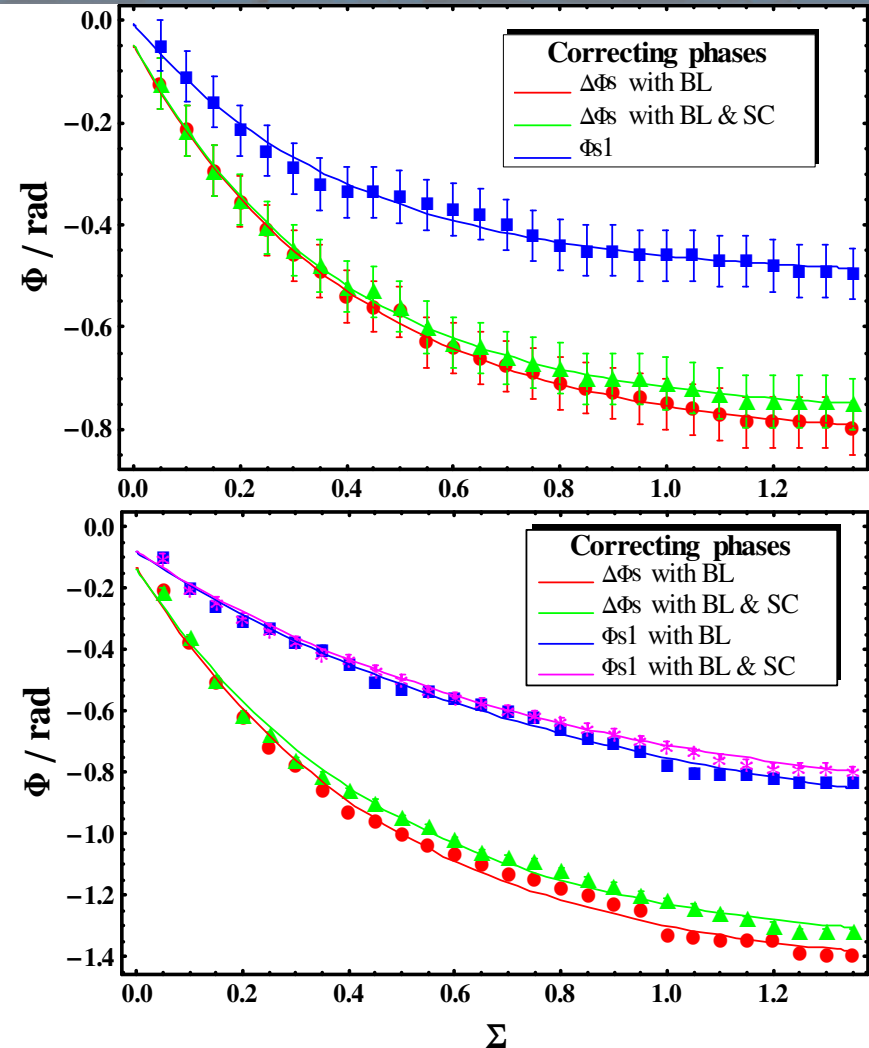


Double harmonic RF system

Ferrite insert impedance table (Finemet FT3-M)

- The correction phases are smaller with sc
- The correction phases are smaller with less higher harmonics

Table with constant impedance with value
@ $f_{\text{RF}} = 1.57 \text{ MHz}$.



Outlook and conclusion

- The difference of the behavior between a double harmonic system with $\alpha = 0.5$ and $\alpha = 1.0$ has to be better understood.
- The dependency of the correction phases over the quality factor has to be better understood
- Space charge can be compensated by an insert in SIS-18 and SIS-100.
- The impedances of broadband cavities and inserts are comparable
- For cavities beam loading is relevant
- For inserts without amplifier potential-well distortion is relevant
- In single harmonic RF systems only phase shifts are correctable
- In double harmonic RF systems asymmetries in bunch form and phase shifts are correctable
- Space charge is helpful for these corrections

Conclusion

Thank you for your attention!